

Supplementary information for

Hydrogen sensing properties of FET-type sensors with Pt-In₂O₃ at room temperature

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Table S1. Comparison of the sensing performance towards hydrogen gas of recently reported FET-type sensors. RT: room temperature.

Sensor materials	T(°C)	Deposition method	Response/ Recovery times at H ₂ %	Type	Ref.
Pt-In ₂ O ₃ sensitive gate	RT	inkjet printing	90 s/680 s at 1000 ppm	FET	This work
Monolayer MoS ₂	200	dry viscoelastic stamping	7 min/67 min at 50%	FET	[1]
Pt sensitive gate	240	e-beam	2.5 min/8.85 min at 250 ppm	HEMT	[2]
Pd-Ti/ZnO	100	RF Sputtering	20 s/80 s at 4500 ppm	Schottky TFT	[3]
Pt-Graphene sensitive gate	RT	transfer & e-beam	9.8 min/0.4 min	HEMT	[4]

References

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